## PATENT ABSTRACTS OF JAPAN

(11)Publication number:

09-252059

(43) Date of publication of application: 22.09.1997

(51)Int.CI.

H01L 21/8247

H01L 29/788 H01L 29/792 H01L 29/78

(21)Application number: 08-060621

(71)Applicant: TOSHIBA CORP

(22)Date of filing:

18.03.1996

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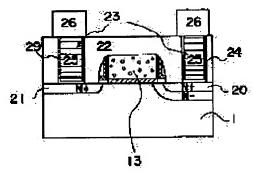
NARUGE KIYOMI

## (54) SEMICONDUCTOR DEVICE

## (57)Abstract:

PROBLEM TO BE SOLVED: To provide a nonvolatile semiconductor device which can be micronized in size and enhanced in reliability, dispensing with a selection transistor.

SOLUTION: A nonvolatile semiconductor memory device is composed of a second conductivity—type first diffusion layer 20, a second conductivity—type second diffusion layer 21, and a gate electrode formed on a part of a channel region located between the diffusion layers 20, 21 and on a part of the first diffusion layer through of a first insulating film, wherein a part of a second insulating film of at least two—layered structure formed on the channel region between the gate electrode and the second diffusion layer 21 of 30nm or less in thickness is made to serve as a charge storage layer.



## LEGAL STATUS

[Date of request for examination]

14.06.2000

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

Date of final disposal for application

[Patent number]

[Date of registration]